

Abstract of Disclosure

Provided with a semiconductor device including: a
semiconductor substrate having a first conductivity type; a
first well having a second conductivity type formed in a first
5 region in a major surface of the semiconductor substrate; a
second well having the first conductivity type formed in a
second region in the major surface of the semiconductor
substrate; a first MOS transistor having the first
conductivity type and a first contact region having the second
10 conductivity type formed in the first well; a second MOS
transistor having the second conductivity type and a second
contact region having the second conductivity type formed in
the second well; a heavily doped region of buried layer having
the second conductivity type formed at a portion corresponding
15 to the first contact region in the first well; and a heavily
doped region of buried layer having the first conductivity
type formed at a portion corresponding to the second contact
region in the second well.